



MCR100-8 1A Sensitive SCR

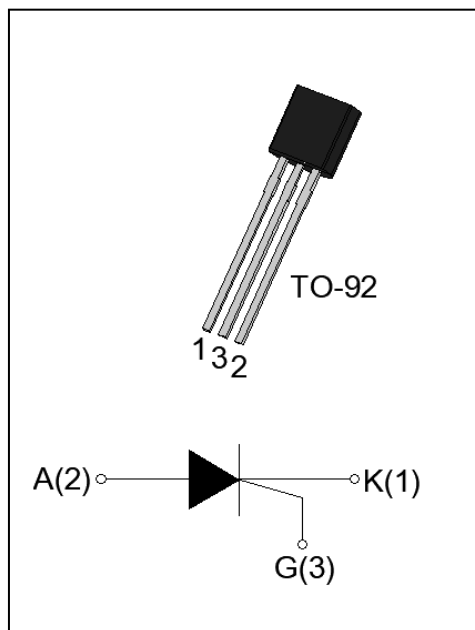
Rev.A.2.0

DESCRIPTION:

The MCR100-8 SCR provides high dV/dt rate with strong resistance to electromagnetic interface. It is especially recommended for use on residual current circuit breaker, straight hair, igniter etc. Package TO-92 is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM} / V_{RRM}	800	V
I_{GT}	≤ 200	μA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range	T_j	-40-125 ^①	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	800	V
Average on-state current ($T_c \leq 54^{\circ}C$)	$I_{T(AV)}$	0.6	A
RMS on-state current ($T_c \leq 54^{\circ}C$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^{\circ}C$)	I_{TSM}	12	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^{\circ}C$)		13	
I^2t value for fusing ($t_p=10ms, T_j=25^{\circ}C$)	I^2t	0.72	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=125^{\circ}C$)	di/dt	100	$A/\mu s$
Peak gate current ($t_p=20\mu s, T_j=125^{\circ}C$)	I_{GM}	1	A
Average gate power dissipation ($T_j=125^{\circ}C$)	$P_{G(AV)}$	0.1	W

Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	1	kV

NOTE 1: When we parallel connect a $\leq 1\text{K}\Omega$ resistor between Gate and Cathode, the T_j can reach 125°C ; if without this resistor, the T_j only can reach 110°C .

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	-	40	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	5	mA
I_H	$I_T=0.05\text{A}$	-	-	4	mA
dV/dt	$V_D=600\text{V}$ $T_j=125^\circ\text{C}$ $R_{GK}=1\text{K}\Omega$	200	-	-	$\text{V}/\mu\text{s}$
	$V_D=600\text{V}$ $T_j=125^\circ\text{C}$ $R_{GK}=220\Omega$	500	-	-	
t_{on}	$I_G=10\text{mA}$ $I_A=20\text{mA}$ $I_R=2\text{mA}$	-	2	-	μs
t_{off}	$T_j=25^\circ\text{C}$	-	50	-	μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_T=2\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.4	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.8	V
R_D	Dynamic Resistance	$T_j=125^\circ\text{C}$	0.1	Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	0.2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	61	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (DC)	130	$^\circ\text{C}/\text{W}$

MARKING

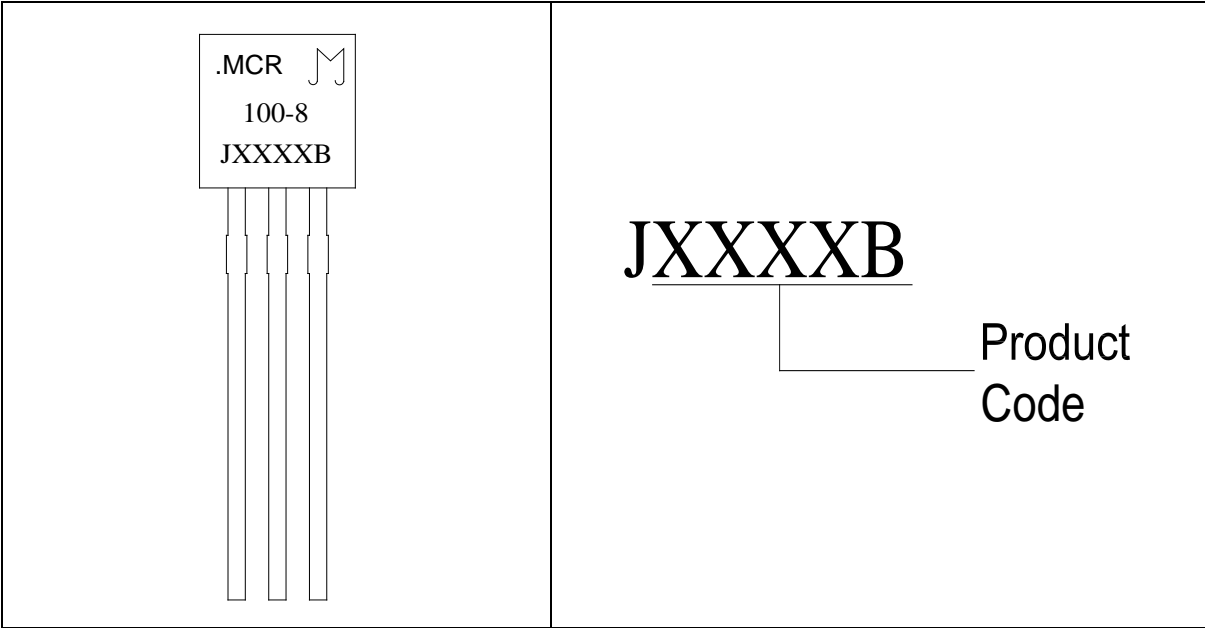


FIG.1: Maximum power dissipation versus RMS on-state current

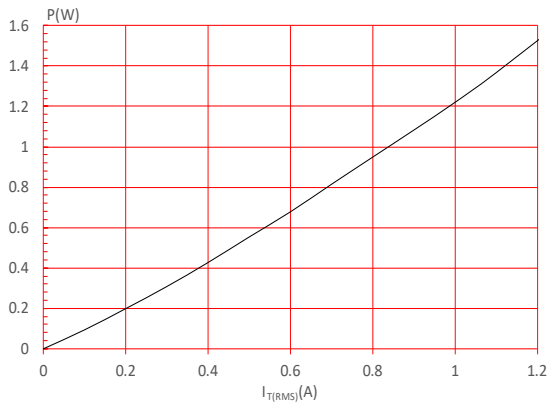


FIG.2: RMS on-state current versus case temperature

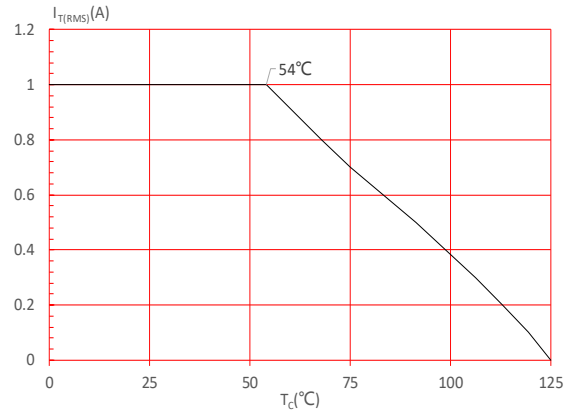


FIG.3: Surge peak on-state current versus number of cycles

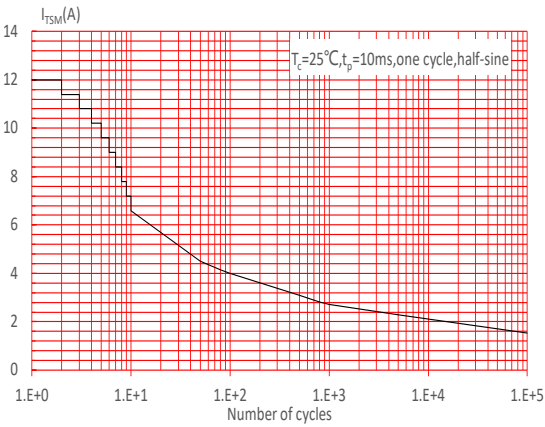


FIG.4: On-state characteristics

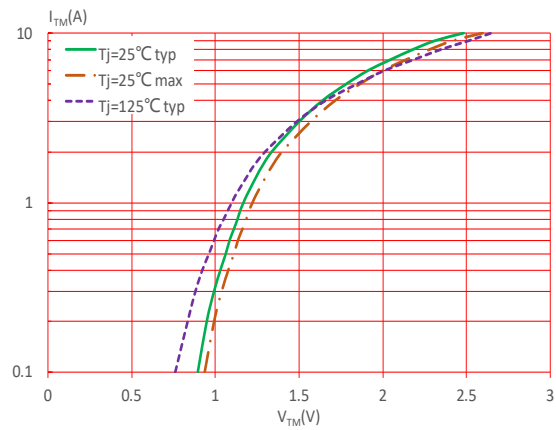


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

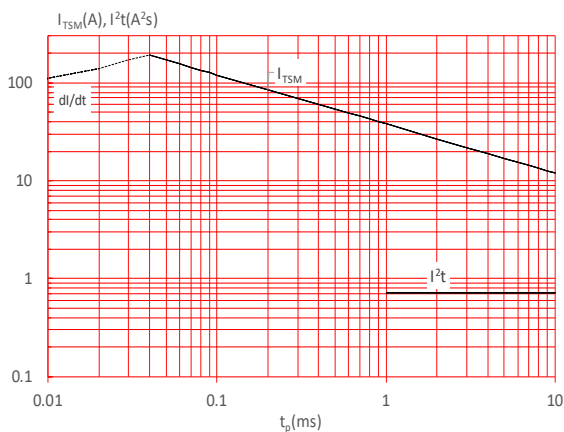


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

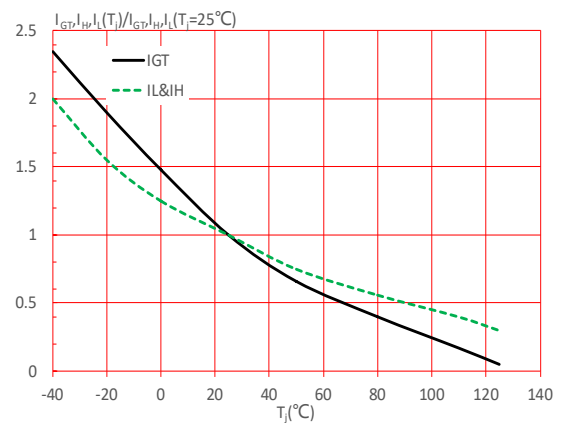
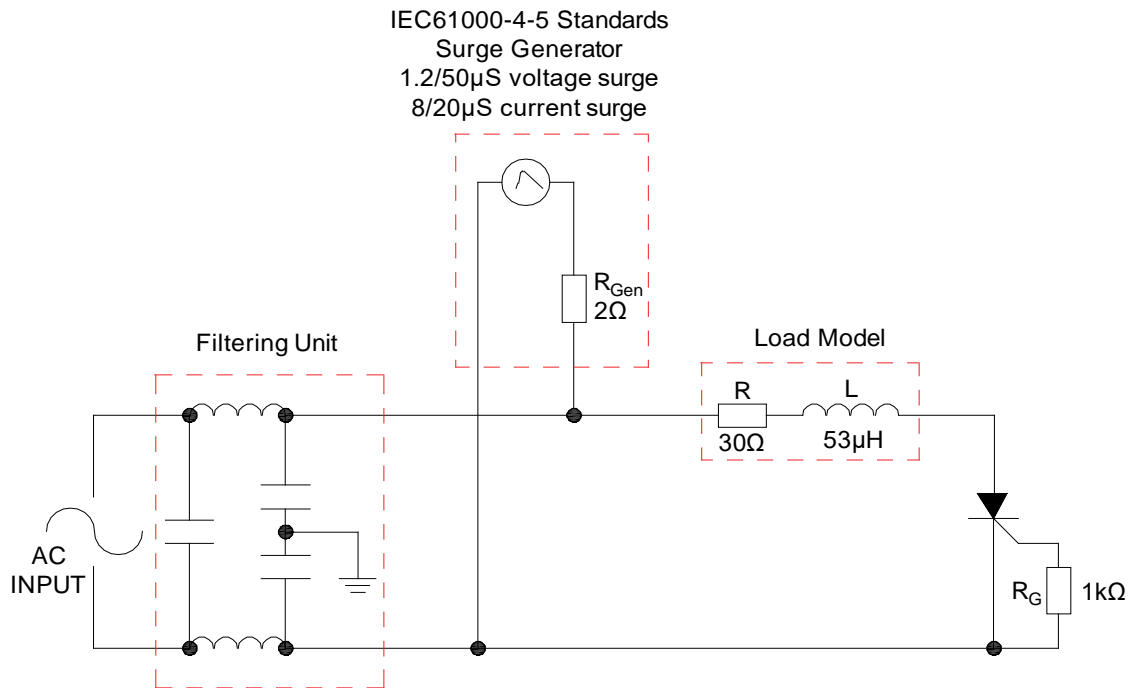


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

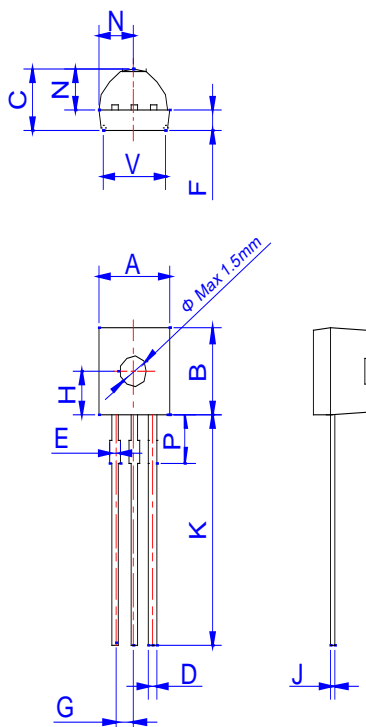
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(μ A)	Package	Base qty. (pcs)	Delivery mode
MCR100-8	800	≤ 200	TO-92	1,000	Bulk Pack
MCR100-8-TR				2,000	Tape & Reel

Document Revision History

Date	Revision	Changes
May.23, 2023	A.1.0	Last update
Mar.28, 2025	A.2.0	Renew PACKAGE MECHANICAL DATA

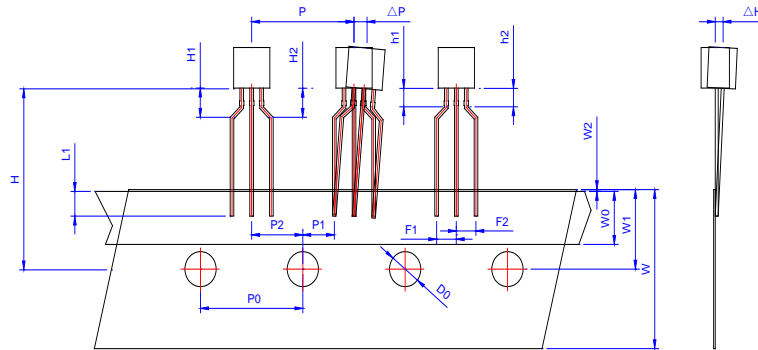
PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.50		0.70	0.020		0.028
F	1.10		1.30			0.051
G	1.10		1.40	0.043		0.055
H	2.20		2.40	0.087		0.094
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.80		2.30	0.071		0.091
V	4.10		4.50	0.161		0.177

DELIVERY MODE

PACKAGE	OUTLINE	BAG (PCS)	INNER BOX (PCS)	CARTON BOX (PCS)
TO-92	Bulk Pack	1,000	10,000	50,000



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
P	12.40	12.70	13.00	0.488	0.500	0.512
P0	12.40	12.70	13.00	0.488	0.500	0.512
P1	3.55	3.85	4.15	0.140	0.152	0.163
P2	5.95	6.35	6.75	0.233	0.250	0.265
ΔP	-1.00	0	1.00	-0.039	0	0.039
F1、F2	2.30	2.50	2.70	0.090	0.098	0.106
F1-F2	-0.10	0	0.10	-0.004	0	0.004
W	17.50	18.00	19.00	0.689	0.709	0.748
W0	5.50	6.00	6.50	0.217	0.236	0.256
W1	8.50	9.00	9.50	0.335	0.354	0.374
W2			1.00			0.039
D0	3.80	4.00	4.20	0.150	0.157	0.165
ΔH	-1.00	0	1.00	-0.039	0	0.039
L1	2.50			0.098		
H	18.00	19.00	20.00	0.709	0.748	0.787
H1、H2			3.00			0.119
H1-H2	-0.50		0.50	-0.020		0.020
h1、h2			1.00			0.040
h1-h2	-0.20		0.20	-0.008		0.008

PACKAGE	OUTLINE	REEL (PCS)	INNER BOX (PCS)	CARTON BOX (PCS)
TO-92	Tape & Reel	/	2,000	20,000

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